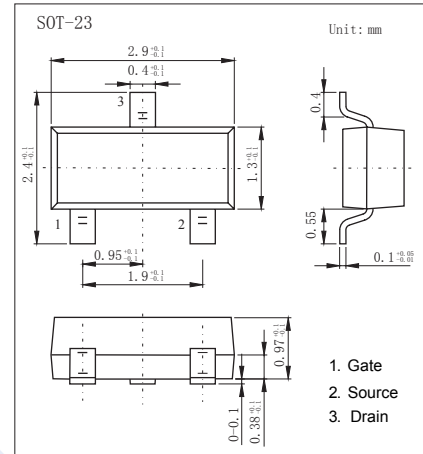
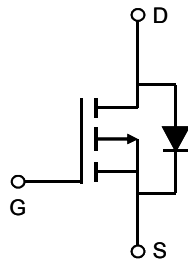


P-Channel MOSFET

KI3419P

■ Features

- $V_{DS} = -12V$
- $I_D = -4.1 A$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 45m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 60m\Omega$ ($V_{GS} = -2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-4.1	A
Power Dissipation	P_D	1.4	W
Thermal Resistance.Junction- to-Ambient	R_{thJA}	125	$^\circ C/W$
Thermal Resistance.Junction- to-Case	R_{thJC}	60	
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250\mu A, V_{GS} = 0V$	-12			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$			-10	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4.1A$			45	m Ω
		$V_{GS} = -2.5V, I_D = -3A$			60	
Diode Forward Voltage	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1.15	V

■ Marking

Marking	T3419
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